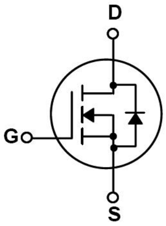
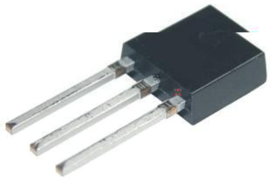
TO-251 N MOS N-CHANNEL MOSFET in a TO-251 Plastic Package.

Low $R_{DS(on)}$,low gate charge, low C_{rss}, fast speed switching.

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

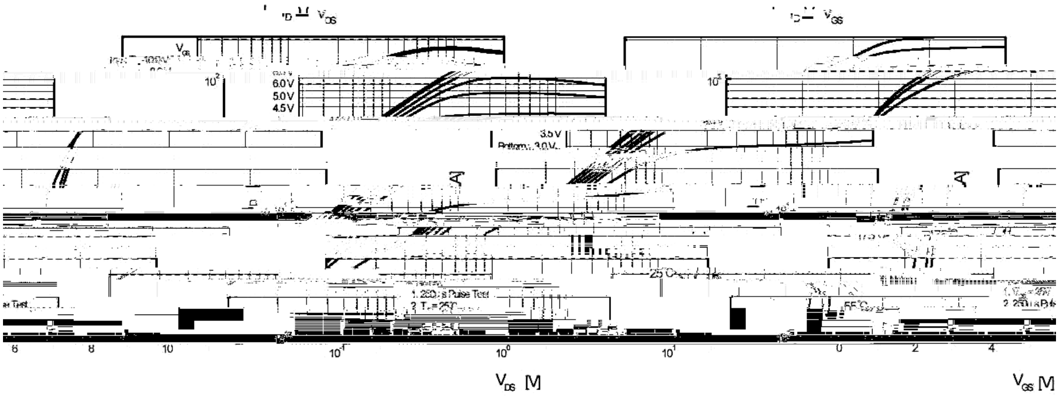


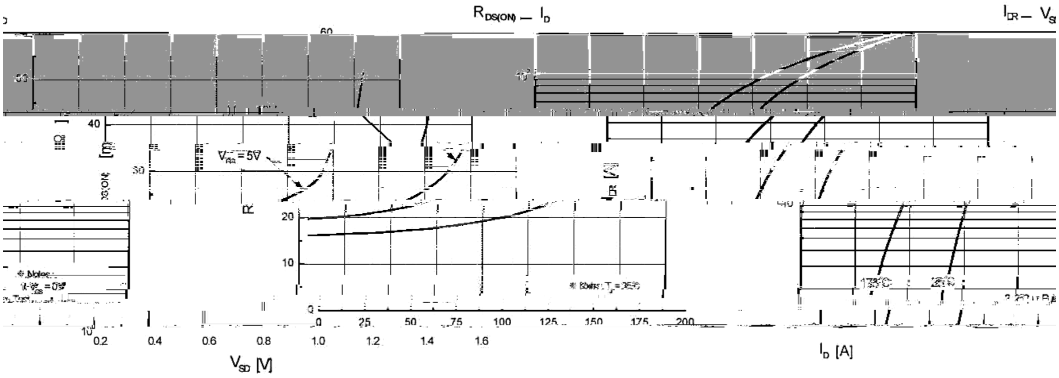


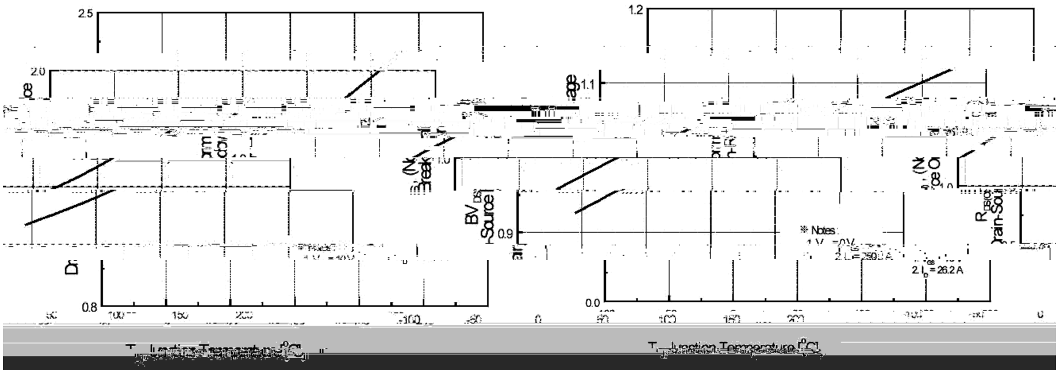
PIN1 G PIN 2 D PIN 3 S

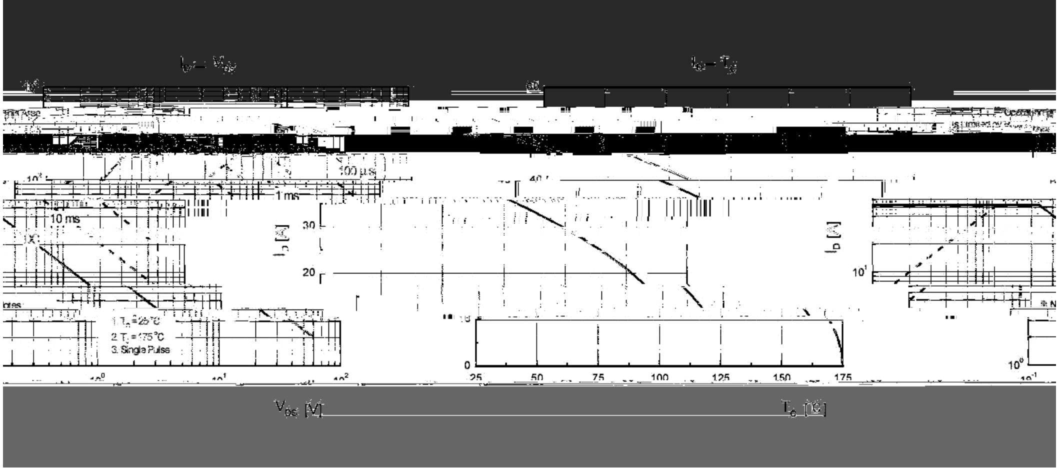
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain Current	I_D(Tc=25)	50	A
Drain Current	I_D(Tc=100)	35.4	A
Drain Current Pulsed	I_{DM}	200	A
Gate-Source Voltage	V_{GS}	±20	V
Single Pulsed Avalanche Energy	E_{AS}	490	mJ
Repetitive Avalanche Energy	E_{AR}	12	mJ
Power Dissipation	P_D(Tc=25)	85	W
Junction Temperature Range	T_j	150	
Storage Temperature Range	TD7j j		

/ Electrical Characteristic Curve

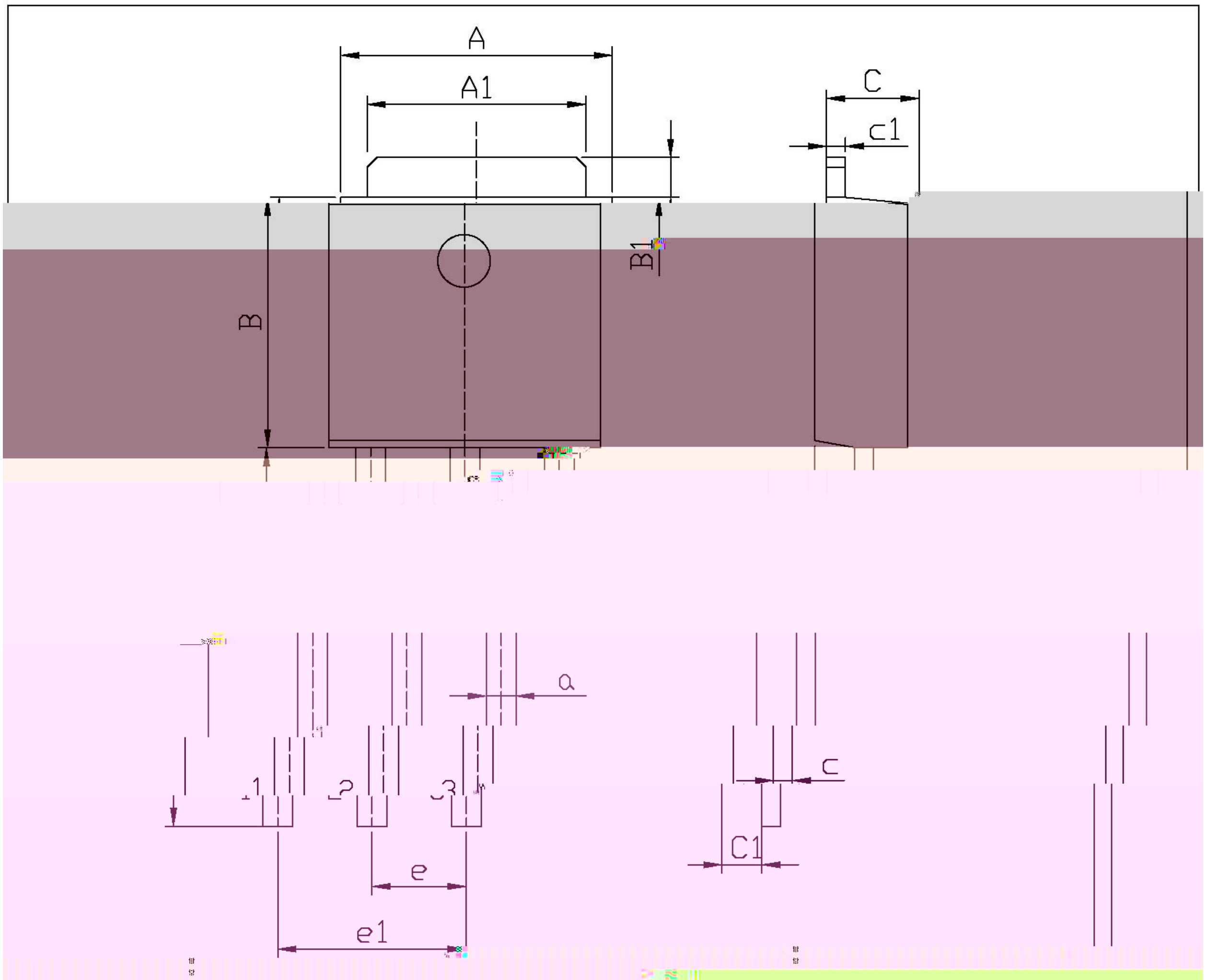




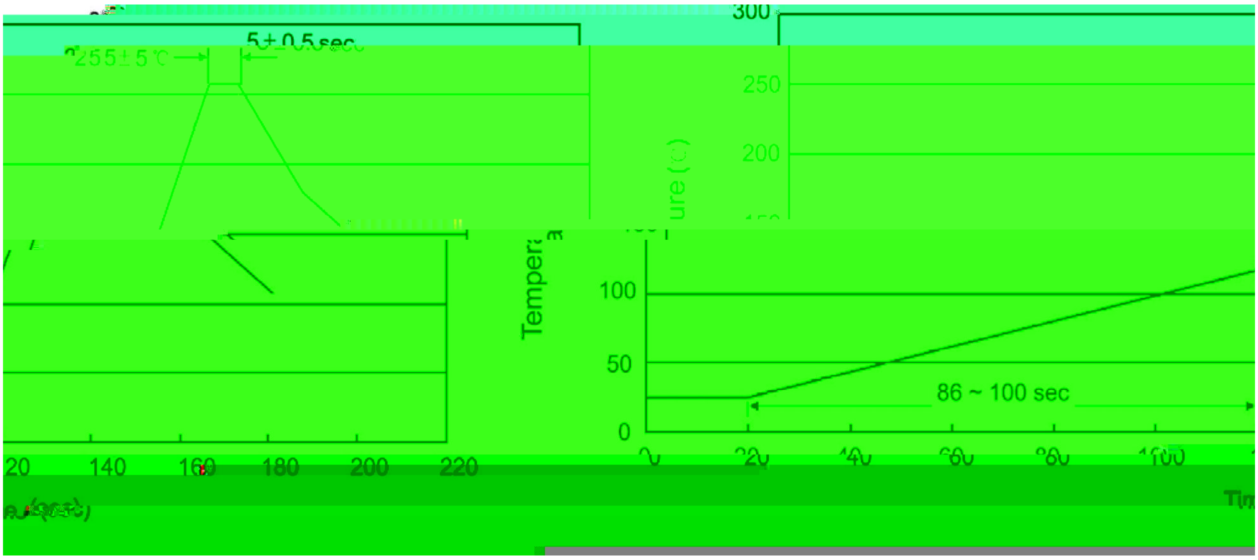




/ Package Dimensions



( ) / Temperature Profile for Dip Soldering(Pb-Free)



1 25 150 60 90sec;
2 255 5 5 0.5sec;
3 2 10 /sec.

Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255 5 , Duration:5 0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱